

# 1 $\Omega$ Typical On Resistance, $\pm 5$ V, +12 V, +5 V, and +3.3 V Dual SPDT Switches

ADG1636

#### **FEATURES**

1 Ω typical on resistance
0.2 Ω on resistance flatness
±3.3 V to ±8 V dual supply operation
3.3 V to 16 V single supply operation
No V<sub>L</sub> supply required
3 V logic-compatible inputs
Rail-to-rail operation
Continuous current per channel
LFCSP package: 385 mA

LFCSP package: 385 mA TSSOP package: 238 mA

16-lead TSSOP and 16-lead, 4 mm × 4 mm LFCSP

#### **APPLICATIONS**

Communication systems
Medical systems
Audio signal routing
Video signal routing
Automatic test equipment
Data acquisition systems
Battery-powered systems
Sample-and-hold systems
Relay replacements

#### **GENERAL DESCRIPTION**

The ADG1636 is a monolithic CMOS device containing two independently selectable single-pole/double-throw (SPDT) switches. An EN input is used to enable or disable the device. When disabled, all channels are switched off. Each switch conducts equally well in both directions when on and has an input signal range that extends to the supplies. In the off condition, signal levels up to the supplies are blocked. Both switches exhibit break-before-make switching action for use in multiplexer applications.

The ultralow on resistance of these switches make them ideal solutions for data acquisition and gain switching applications where low on resistance and distortion is critical. The on resistance profile is very flat over the full analog input range, ensuring excellent linearity and low distortion when switching audio signals.

The CMOS construction ensures ultralow power dissipation, making the parts ideally suited for portable and battery-powered instruments.

#### Rev. A

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#### **FUNCTIONAL BLOCK DIAGRAMS**

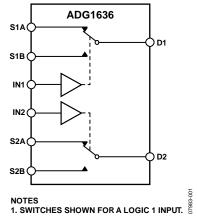


Figure 1. 16-Lead TSSOP

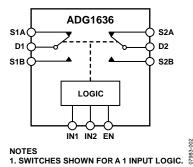


Figure 2. 16-Lead LFCSP

#### **PRODUCT HIGHLIGHTS**

- 1.  $1.6 \Omega$  maximum on resistance over temperature.
- 2. Minimum distortion: THD + N = 0.007%.
- 3. 3 V logic-compatible digital inputs:  $V_{INH} = 2.0 \text{ V}$ ,  $V_{INL} = 0.8 \text{ V}$ .
- 4. No V<sub>L</sub> logic power supply required.
- 5. Ultralow power dissipation: <16 nW.
- 6. 16-lead TSSOP and 16-lead 4 mm × 4 mm LFCSP.

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### **REVISION HISTORY**

9/09—Rev. 0 to Rev. A
Changes to Table 4
1/09—Revision 0: Initial Version

# **SPECIFICATIONS**

## **±5 V DUAL SUPPLY**

 $V_{\text{DD}}$  = +5 V  $\pm$  10%,  $V_{\text{SS}}$  = -5 V  $\pm$  10%, GND = 0 V, unless otherwise noted.

Table 1.

Parameter	25°C	−40°C to +85°C	−40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			$V_{\text{DD}}$ to $V_{\text{SS}}$	V	
On Resistance (R <sub>ON</sub> )	1			Ω typ	$V_S = \pm 4.5 \text{ V, } I_S = -10 \text{ mA; see Figure 23}$
	1.2	1.4	1.6	Ω max	$V_{DD} = \pm 4.5 \text{ V}, V_{SS} = \pm 4.5 \text{ V}$
On Resistance Match Between Channels (ΔR <sub>ON</sub> )	0.04			Ωtyp	$V_S = \pm 4.5 \text{ V, } I_S = -10 \text{ mA}$
	0.08	0.09	0.1	Ω max	
On Resistance Flatness (R <sub>FLAT(ON)</sub> )	0.2			Ωtyp	$V_S = \pm 4.5 \text{ V, } I_S = -10 \text{ mA}$
	0.25	0.29	0.34	Ω max	·
LEAKAGE CURRENTS					$V_{DD} = +5.5 \text{ V}, V_{SS} = -5.5 \text{ V}$
Source Off Leakage, Is (Off)	±0.1			nA typ	•
					$V_S = \pm 4.5 \text{ V}, V_D = \mp 4.5 \text{ V}; \text{ see Figure 24}$
	±0.25	±1	±4	nA max	
Drain Off Leakage, I <sub>D</sub> (Off)	±0.1			nA typ	$V_S = \pm 4.5 \text{V}, V_D = \mp 4.5 \text{ V}; \text{ see Figure 24}$
	±0.25	±2	±10	nA max	
Channel On Leakage, ID, IS (On)	±0.3			nA typ	$V_S = V_D = \pm 4.5 \text{ V}$ ; see Figure 25
2.12	±0.6	±2	±12	nA max	
DIGITAL INPUTS					
Input High Voltage, V <sub>INH</sub>			2.0	V min	
Input Low Voltage, V <sub>INL</sub>			0.8	V max	
Input Current, I <sub>INL</sub> or I <sub>INH</sub>	0.005		0.0	μA typ	$V_{IN} = V_{GND}$ or $V_{DD}$
Input carrette, fine of fine	0.003		±0.1	μA max	VIN — VGND OI VDD
Digital Input Capacitance, C <sub>IN</sub>	5		±0.1	pF typ	
DYNAMIC CHARACTERISTICS <sup>1</sup>	-			pi typ	
Transition Time, transition	130			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
Transition Time, transition	209	245	273	ns max	$V_S = 2.5 \text{ V}$ ; see Figure 30
ton (EN)	119	243	2/3		$R_L = 300 \Omega, C_L = 35 pF$
ton (EIV)	148	166	176	ns typ ns max	$V_S = 2.5 \text{ V}$ ; see Figure 30
+ (ENI)	182	100	170		$R_L = 300 \Omega, C_L = 35 pF$
toff (EN)	228	259	281	ns typ	$V_S = 2.5 \text{ V}$ ; see Figure 30
Break-Before-Make Time Delay, t <sub>D</sub>		239	201	ns max	_
Break-Beiore-Make Time Delay, LD	30		17	ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	120		17	ns min	$V_{S1} = V_{S2} = 2.5 \text{ V}$ ; see Figure 31
Charge Injection	130			pC typ	$V_S = 0 \text{ V}, R_S = 0 \Omega, C_L = 1 \text{ nF}; \text{ see Figure 32}$
Off Isolation	70			dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; see Figure 26
Channel-to-Channel Crosstalk	90			dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; see Figure 28
Total Harmonic Distortion + Noise (THD + N)	0.007			% typ	$R_L = 110 \ \Omega$ , 5 V p-p, f = 20 Hz to 20 kHz; see Figure 29
−3 dB Bandwidth	25			MHz typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ ; see Figure 27
C <sub>s</sub> (Off)	68			pF typ	$V_S = 0 \text{ V, } f = 1 \text{ MHz}$
C <sub>D</sub> (Off)	127			pF typ	$V_S = 0 V, f = 1 MHz$
$C_D$ , $C_S$ (On)	220			pF typ	$V_S = 0 V, f = 1 MHz$
POWER REQUIREMENTS			_		$V_{DD} = +5.5 \text{ V}, V_{SS} = -5.5 \text{ V}$
$I_{DD}$	0.001			μA typ	Digital inputs = 0 V or V <sub>DD</sub>
			1.0	μA max	
$V_{DD}/V_{SS}$			±3.3/±8	V min/max	

 $<sup>^{\</sup>mbox{\tiny 1}}$  Guaranteed by design, not subject to production test.

## **12 V SINGLE SUPPLY**

 $V_{\text{DD}}$  = 12 V  $\pm$  10%,  $V_{\text{SS}}$  = 0 V, GND = 0 V, unless otherwise noted.

Table 2.

Parameter	25°C	−40°C to +85°C	−40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			$0V$ to $V_{DD}$	V	
On Resistance (R <sub>ON</sub> )	0.95			Ωtyp	$V_S = 0 \text{ V to } 10 \text{ V}, I_S = -10 \text{ mA}; \text{ see Figure } 23$
	1.1	1.25	1.45	Ω max	$V_{DD} = 10.8 \text{ V}, V_{SS} = 0 \text{ V}$
On Resistance Match Between Channels (ΔR <sub>ON</sub> )	0.03			Ωtyp	$V_S = 10 \text{ V}, I_S = -10 \text{ mA}$
	0.06	0.07	0.08	Ω max	
On Resistance Flatness (R <sub>FLAT(ON)</sub> )	0.2			Ωtyp	$V_S = 0 \text{ V to } 10 \text{ V, } I_S = -10 \text{ mA}$
(12.1(6.1))	0.23	0.27	0.32	Ω max	, , , , , , , , , , , , , , , , , , , ,
LEAKAGE CURRENTS					$V_{DD} = 13.2 \text{ V}, V_{SS} = 0 \text{ V}$
Source Off Leakage, Is (Off)	±0.1			nA typ	$V_s = 1 \text{ V}/10 \text{ V}, V_s = 10 \text{ V}/1 \text{ V}; \text{ see Figure 24}$
55a.55 5.1. <u>15a.1.ag</u> 2, 15 (51.1)	±0.25	±1	±4	nA max	
Drain Off Leakage, I <sub>D</sub> (Off)	±0.23			nA typ	$V_s = 1 \text{ V}/10 \text{ V}, V_s = 10 \text{ V}/1 \text{ V}; \text{ see Figure 24}$
Drain on Leakage, ib (on)	±0.25	±2	±10	nA max	v3=1 v710 v, v3=10 v71 v, see rigate 21
Channel On Leakage, ID, Is (On)	±0.23	<u></u> 2	±10	nA typ	$V_S = V_D = 1 \text{ V or } 10 \text{ V}; \text{ see Figure } 25$
Charmer on Leakage, ID, 13 (OH)	±0.5	±2	±12	nA max	v <sub>3</sub> = v <sub>0</sub> = 1 v or 10 v, see rigate 25
DIGITAL INPUTS	±0.0	<u> </u>	±12	TIA IIIax	
			2.0	V min	
Input High Voltage, VINH					
Input Low Voltage, V <sub>INL</sub>	0.001		8.0	V max	W WW
Input Current, I <sub>INL</sub> or I <sub>INH</sub>	0.001		.01	μA typ	$V_{IN} = V_{GND} \text{ or } V_{DD}$
S: :: II	_		±0.1	μA max	
Digital Input Capacitance, C <sub>IN</sub>	5			pF typ	
DYNAMIC CHARACTERISTICS <sup>1</sup>					
Transition Time, transition	100			ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$
4-10	153	183	206	ns max	$V_S = 8 \text{ V}$ ; see Figure 30
ton (EN)	80			ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$
	95	103	110	ns max	$V_s = 8 \text{ V}$ ; see Figure 30
t <sub>off</sub> (EN)	133			ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$
	161	187	210	ns max	$V_S = 8 \text{ V}$ ; see Figure 30
Break-Before-Make Time Delay, t <sub>D</sub>	25			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
			17	ns min	$V_{S1} = V_{S2} = 8 \text{ V}$ ; see Figure 31
Charge Injection	150			pC typ	$V_S = 6 \text{ V}$ , $R_S = 0 \Omega$ , $C_L = 1 \text{ nF}$ ; see Figure 32
Off Isolation	70			dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; see Figure 26
Channel-to-Channel Crosstalk	90			dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; see Figure 28
Total Harmonic Distortion + Noise (THD + N)	0.013			% typ	$R_L = 110~\Omega$ , 5 V p-p, f = 20 Hz to 20 kHz; see Figure 29
–3 dB Bandwidth	27			MHz typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ ; see Figure 27
C <sub>s</sub> (Off)	65			pF typ	$V_S = 6 \text{ V, } f = 1 \text{ MHz}$
C <sub>D</sub> (Off)	120			pF typ	$V_S = 6 \text{ V, } f = 1 \text{ MHz}$
$C_D$ , $C_S$ (On)	216			pF typ	$V_{S} = 6 \text{ V, } f = 1 \text{ MHz}$
POWER REQUIREMENTS					$V_{DD} = 12 \text{ V}$
I <sub>DD</sub>	0.001			μA typ	Digital inputs = 0 V or V <sub>DD</sub>
			1	μA max	
$I_{DD}$	230		•	μΑ typ	Digital inputs = 5 V
.00	-30		360	μA max	2.3.41.1111443 3 1

 $<sup>^{\</sup>rm 1}$  Guaranteed by design, not subject to production test.

## **5 V SINGLE SUPPLY**

 $V_{\text{DD}}$  = 5 V  $\pm$  10%,  $V_{\text{SS}}$  = 0 V, GND = 0 V, unless otherwise noted.

Table 3.

Davamentor	2500	–40°C to	−40°C to	Unit	Tost Conditions/Comments
Parameter	25°C	+85°C	125°C	Unit	Test Conditions/Comments
ANALOG SWITCH			01/4-1/	.,	
Analog Signal Range	4 7		$0 V to V_{DD}$	V	V 0V: 45VI 10 A F: 22
On Resistance (R <sub>ON</sub> )	1.7			Ωtyp	$V_S = 0 \text{ V to } 4.5 \text{ V, } I_S = -10 \text{ mA; see Figure 23}$
	2.15	2.4	2.7	Ω max	$V_{DD} = 4.5 \text{ V}, V_{SS} = 0 \text{ V}$
On Resistance Match Between Channels ( $\Delta R_{ON}$ )	0.05			Ωtyp	$V_S = 0 \text{ V to } 4.5 \text{ V, } I_S = -10 \text{ mA}$
	0.09	0.12	0.15	Ω max	
On Resistance Flatness (R <sub>FLAT(ON)</sub> )	0.4			Ωtyp	$V_S = 0 \text{ V to } 4.5 \text{ V, } I_S = -10 \text{ mA}$
	0.53	0.55	0.6	Ω max	
LEAKAGE CURRENTS					$V_{DD} = 5.5 \text{ V}, V_{SS} = 0 \text{ V}$
Source Off Leakage, I <sub>s</sub> (Off)	±0.05			nA typ	$V_S = 1 \text{ V/4.5 V, } V_D = 4.5 \text{ V/1 V; see Figure 24}$
	±0.25	±1	±4	nA max	
Drain Off Leakage, I <sub>D</sub> (Off)	±0.05			nA typ	$V_S = 1 \text{ V/4.5 V, } V_D = 4.5 \text{ V/1 V; see Figure 24}$
	±0.25	±2	±10	nA max	
Channel On Leakage, ID, IS (On)	±0.1			nA typ	$V_S = V_D = 1 \text{ V or } 4.5 \text{ V}$ ; see Figure 25
	±0.6	±2	±12	nA max	
DIGITAL INPUTS					
Input High Voltage, V <sub>INH</sub>			2.0	V min	
Input Low Voltage, V <sub>INL</sub>			0.8	V max	
Input Current, I <sub>INL</sub> or I <sub>INH</sub>	0.001			μA typ	$V_{IN} = V_{GND}$ or $V_{DD}$
			±0.1	μA max	
Digital Input Capacitance, C <sub>IN</sub>	5			pF typ	
DYNAMIC CHARACTERISTICS <sup>1</sup>					
Transition Time, transition	160			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	271	319	355	ns max	$V_s = 2.5 \text{ V}$ ; see Figure 30
ton (EN)	132			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	172	185	201	ns max	$V_S = 2.5 \text{ V}$ ; see Figure 30
t <sub>OFF</sub> (EN)	210			ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$
	268	313	345	ns max	$V_s = 2.5 \text{ V}$ ; see Figure 30
Break-Before-Make Time Delay, t <sub>D</sub>	30			ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$
Steam Service make time Seray, to			17	ns min	$V_{S1} = V_{S2} = 2.5 \text{ V}$ ; see Figure 31
Charge Injection	70		.,	pC typ	$V_s = 2.5 \text{ V}, R_s = 0 \Omega, C_L = 1 \text{ nF}; \text{ see Figure } 32$
Off Isolation	70			dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 100 kHz$ ;
on Boldton	/ 0			abtyp	see Figure 26
Channel-to-Channel Crosstalk	90			dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 100 kHz$ ; see Figure 28
Total Harmonic Distortion + Noise (THD + N)	0.09			% typ	$R_L = 110 \Omega$ , $f = 20 Hz$ to $20 kHz$ , $V_S = 3.5 V$ p- $\mu$ see Figure 29
–3 dB Bandwidth	26			MHz typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ ; see Figure 27
C <sub>s</sub> (Off)	76			pF typ	$V_S = 2.5 \text{ V, } f = 1 \text{ MHz}$
C <sub>D</sub> (Off)	145			pF typ	$V_S = 2.5 \text{ V, } f = 1 \text{ MHz}$
C <sub>D</sub> , C <sub>s</sub> (On)	237			pF typ	$V_S = 2.5 \text{ V, } f = 1 \text{ MHz}$
POWER REQUIREMENTS				15. 5/16	$V_{DD} = 5.5 \text{ V}$
IDD	0.001			μA typ	Digital inputs = $0 \text{ V or V}_{DD}$
-00	0.501	1.0	1.0	μA max	2.3.3

 $<sup>^{\</sup>mbox{\tiny 1}}$  Guaranteed by design, not subject to production test.

## **3.3 V SINGLE SUPPLY**

 $V_{\text{DD}}$  = 3.3 V,  $V_{\text{SS}}$  = 0 V, GND = 0 V, unless otherwise noted.

Table 4.

Parameter	25°C	−40°C to +85°C	−40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			$0VtoV_{DD}$	V	
On Resistance (R <sub>ON</sub> )	3.2	3.4	3.6	Ωtyp	$V_S = 0 \text{ V to } V_{DD}$ , $I_S = -10 \text{ mA}$ ; see Figure 23
					$V_{DD} = 3.3 \text{ V, } V_{SS} = 0 \text{ V}$
On Resistance Match Between Channels ( $\Delta R_{ON}$ )	0.06	0.07	0.08	Ωtyp	$V_S = 0 \text{ V to } V_{DD}, I_S = -10 \text{ mA}$
On Resistance Flatness (R <sub>FLAT(ON)</sub> )	1.2	1.3	1.4	Ωtyp	$V_S = 0 \text{ V to } V_{DD}, I_S = -10 \text{ mA}$
LEAKAGE CURRENTS					$V_{DD} = 3.6 \text{ V}, V_{SS} = 0 \text{ V}$
Source Off Leakage, Is (Off)	±0.02			nA typ	$V_S = 0.6 \text{ V/3 V}, V_D = 3 \text{ V/0.6 V}$ ; see Figure 24
	±0.25	±1	±4	nA max	
Drain Off Leakage, I <sub>D</sub> (Off)	±0.02			nA typ	$V_S = 0.6 \text{ V/3 V}, V_D = 3 \text{ V/0.6 V}; \text{ see Figure 24}$
	±0.25	±2	±10	nA max	
Channel On Leakage, ID, Is (On)	±0.05			nA typ	$V_S = V_D = 0.6 \text{ V or 3 V; see Figure 25}$
	±0.6	±2	±12	nA max	
DIGITAL INPUTS					
Input High Voltage, V <sub>INH</sub>			2.0	V min	
Input Low Voltage, V <sub>INL</sub>			0.8	V max	
Input Current, I <sub>INL</sub> or I <sub>INH</sub>	0.001			μA typ	$V_{IN} = V_{GND}$ or $V_{DD}$
			±0.1	μA max	
Digital Input Capacitance, C <sub>IN</sub>	5			pF typ	
DYNAMIC CHARACTERISTICS <sup>1</sup>					
Transition Time, trransition	275			ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$
	449	506	550	ns max	$V_S = 1.5 \text{ V}$ ; see Figure 30
ton (EN)	225			ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$
	306	327	338	ns max	$V_S = 1.5 \text{ V}$ ; see Figure 30
toff (EN)	340			ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$
	454	512	553	ns max	$V_S = 1.5 \text{ V}$ ; see Figure 30
Break-Before-Make Time Delay, t <sub>D</sub>	50			ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$
			28	ns min	$V_{S1} = V_{S2} = 1.5 \text{ V}$ ; see Figure 31
Charge Injection	50			pC typ	$V_S = 1.5 \text{ V}, R_S = 0 \Omega, C_L = 1 \text{ nF; see Figure 32}$
Off Isolation	70			dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 100 kHz$ ; see Figure 26
Channel-to-Channel Crosstalk	90			dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 100 kHz$ ; see Figure 28
Total Harmonic Distortion + Noise (THD + N)	0.19			% typ	$R_L = 33 \Omega$ , $f = 20 Hz$ to $20 kHz$ , $V_S = 2 V p-p$ ; see Figure 29
–3 dB Bandwidth	26			MHz typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ ; see Figure 27
C <sub>s</sub> (Off)	80			pF typ	$V_S = 1.5 \text{ V, } f = 1 \text{ MHz}$
C <sub>D</sub> (Off)	153			pF typ	$V_S = 1.5 \text{ V, } f = 1 \text{ MHz}$
$C_D$ , $C_S$ (On)	243			pF typ	$V_S = 1.5 \text{ V, } f = 1 \text{ MHz}$
POWER REQUIREMENTS					V <sub>DD</sub> = 3.6 V
IDD	0.001			μA typ	Digital inputs = 0 V or V <sub>DD</sub>
		1.0	1.0	μA max	
$V_{DD}$			3.3/16	V min/max	

 $<sup>^{\</sup>mbox{\tiny 1}}$  Guaranteed by design, not subject to production test.

## CONTINUOUS CURRENT PER CHANNEL, S OR D

Table 5.

Parameter	25°C	85°C	125°C	Unit
CONTINUOUS CURRENT, S OR D				
$V_{DD} = +5 \text{ V}, V_{SS} = -5 \text{ V}$				
TSSOP ( $\theta_{JA} = 150.4$ °C/W)	238	151	88	mA maximum
LFCSP ( $\theta_{JA} = 48.7^{\circ}$ C/W)	385	220	105	mA maximum
$V_{DD} = 12 \text{ V}, V_{SS} = 0 \text{ V}$				
TSSOP ( $\theta_{JA} = 150.4$ °C/W)	280	175	98	mA maximum
LFCSP ( $\theta_{JA} = 48.7^{\circ}$ C/W)	469	259	119	mA maximum
$V_{DD} = 5 \text{ V}, V_{SS} = 0 \text{ V}$				
TSSOP ( $\theta_{JA} = 150.4$ °C/W)	189	126	77	mA maximum
LFCSP ( $\theta_{JA} = 48.7^{\circ}$ C/W)	301	182	98	mA maximum
$V_{DD} = 3.3 \text{ V, } V_{SS} = 0 \text{ V}$				
TSSOP ( $\theta_{JA} = 150.4$ °C/W)	189	130	84	mA maximum
LFCSP ( $\theta_{JA} = 48.7^{\circ}$ C/W)	305	189	105	mA maximum

## **ABSOLUTE MAXIMUM RATINGS**

 $T_A = 25$ °C, unless otherwise noted.

#### Table 6.

Parameter	Rating
V <sub>DD</sub> to V <sub>SS</sub>	18 V
$V_{DD}$ to GND	−0.3 V to +18 V
V <sub>ss</sub> to GND	+0.3 V to -18 V
Analog Inputs <sup>1</sup>	$V_{SS} - 0.3 \text{ V to } V_{DD} + 0.3 \text{ V or}$ 30 mA, whichever occurs first
Digital Inputs <sup>1</sup>	GND $- 0.3 \text{ V}$ to $\text{V}_{DD} + 0.3 \text{ V}$ or 30 mA, whichever occurs first
Peak Current, S or D	850 mA (pulsed at 1 ms, 10% duty cycle maximum)
Continuous Current, S or D <sup>2</sup>	Data + 15%
Operating Temperature Range	
Industrial (Y Version)	−40°C to +125°C
Storage Temperature Range	−65°C to +150°C
Junction Temperature	150°C
16-Lead TSSOP, θ <sub>JA</sub> Thermal Impedance (2-Layer Board)	150.4°C/W
16-Lead LFCSP, θ <sub>JA</sub> Thermal Impedance (4-Layer Board)	48.7°C/W
Reflow Soldering Peak Temperature, Pb free	260°C

<sup>&</sup>lt;sup>1</sup> Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### **ESD CAUTION**



**ESD** (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

<sup>&</sup>lt;sup>2</sup> See Table 5.

# PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

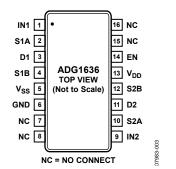


Figure 3. 16-Lead TSSOP Pin Configuration

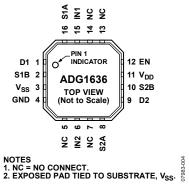


Figure 4. 16-Lead LFCSP Pin Configuration

**Table 7. Pin Function Descriptions** 

Pin No.			
TSSOP	LFCSP	Mnemonic	Description
1	15	IN1	Logic Control Input.
2	16	S1A	Source Terminal. This pin can be an input or output.
3	1	D1	Drain Terminal. This pin can be an input or output.
4	2	S1B	Source Terminal. This pin can be an input or output.
5	3	Vss	Most Negative Power Supply Potential.
6	4	GND	Ground (0 V) Reference.
7, 8, 15, 16	5, 7, 13, 14	NC	No Connection.
9	6	IN2	Logic Control Input.
10	8	S2A	Source Terminal. This pin can be an input or output.
11	9	D2	Drain Terminal. This pin can be an input or output.
12	10	S2B	Source Terminal. This pin can be an input or output.
13	11	$V_{DD}$	Most Positive Power Supply Potential.
14	12	EN	Active High Digital Input. When this pin is low, the device is disabled and all switches are off. When this pin is high, the Ax logic inputs determine the on switches.
N/A	17 (EPAD)	EP (EPAD)	Exposed Pad. Tied to substrate, Vss.

Table 8. ADG1636 TSSOP Truth Table

EN	INx	SxA	SxB
0	Х	Off	Off
1	0	Off	On
1	1	On	Off

Table 9. ADG1636 LFCSP Truth Table

EN	INx	SxA	SxB
0	X	Off	Off
1	0	Off	On
1	1	On	Off

## TYPICAL PERFORMANCE CHARACTERISTICS

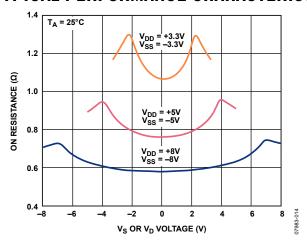


Figure 5. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Dual Supply

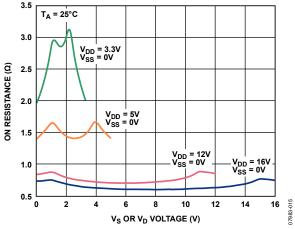


Figure 6. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Single Supply

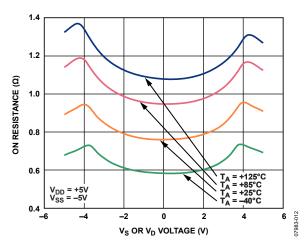


Figure 7. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures,  $\pm 5$  V Dual Supply

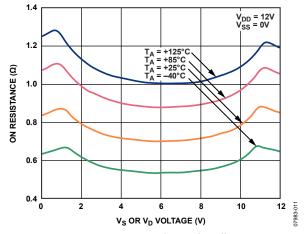


Figure 8. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures, 12 V Single Supply

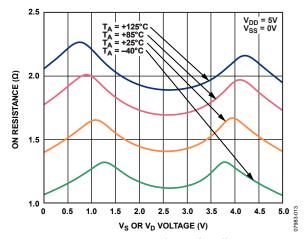


Figure 9. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures, 5 V Single Supply

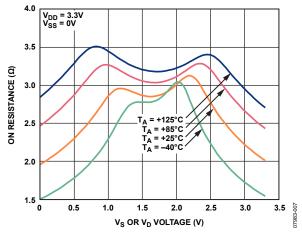


Figure 10. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures, 3.3 V Single Supply

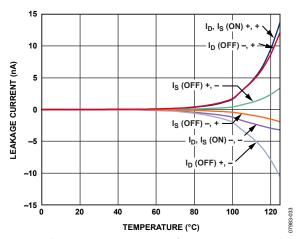


Figure 11. Leakage Currents as a Function of Temperature,  $\pm 5$  V Dual Supply

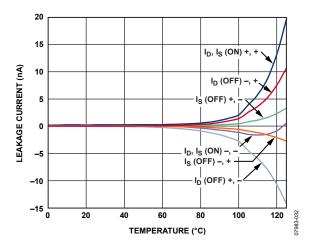


Figure 12. Leakage Currents as a Function of Temperature, 12 V Single Supply

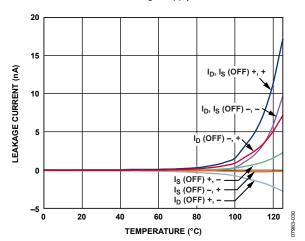


Figure 13. Leakage Currents as a Function of Temperature, 5 V Single Supply

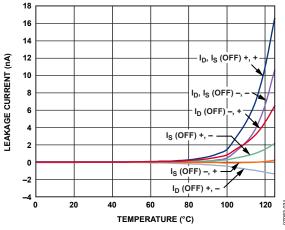


Figure 14. Leakage Currents as a Function of Temperature, 3.3 V Single Supply

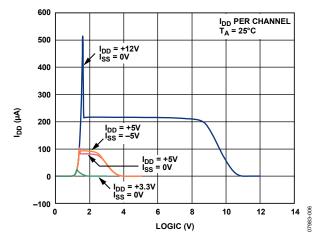


Figure 15. IDD vs. Logic Level

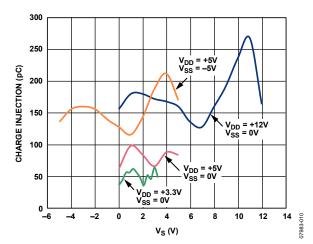


Figure 16. Charge Injection vs. Source Voltage

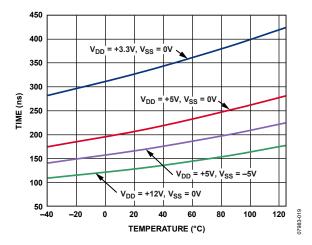


Figure 17.  $t_{ON}/t_{OFF}$  Times vs. Temperature

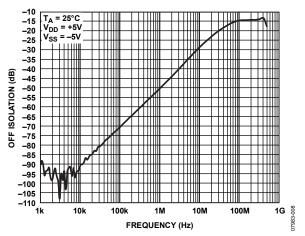


Figure 18. Off Isolation vs. Frequency

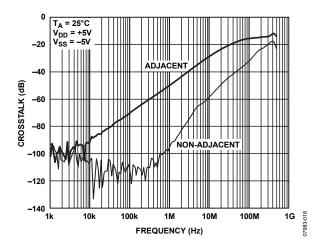


Figure 19. Crosstalk vs. Frequency

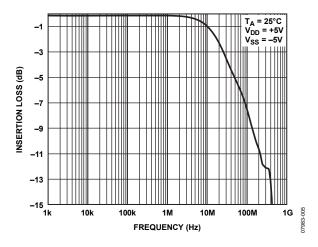


Figure 20. On Response vs. Frequency

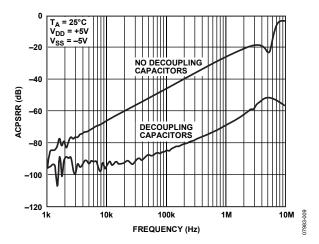


Figure 21. ACPSRR vs. Frequency

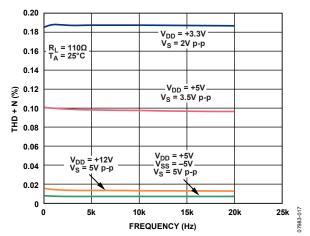
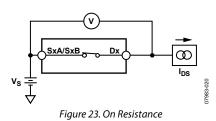
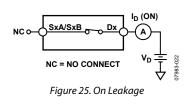


Figure 22. THD + N vs. Frequency

# **TEST CIRCUITS**



 $V_{S} = V_{D} = V_{D$ 



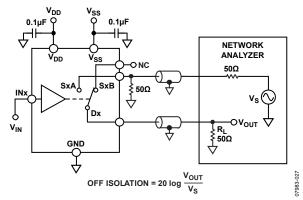


Figure 26. Off Isolation

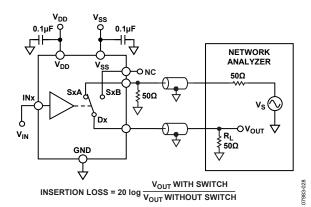


Figure 27. Bandwidth

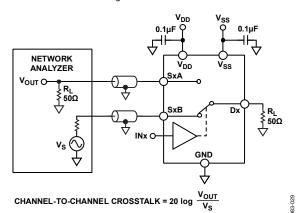


Figure 28. Channel-to-Channel Crosstalk

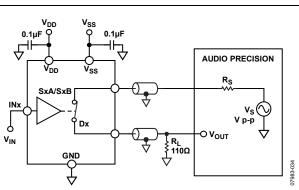


Figure 29. THD + Noise

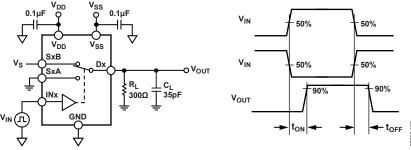


Figure 30. Switching Times

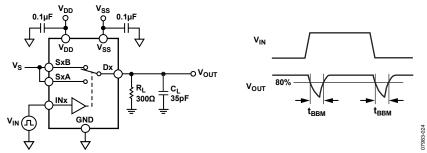


Figure 31. Break-Before-Make Time Delay

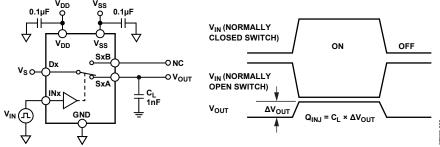


Figure 32. Charge Injection

## **TERMINOLOGY**

 $I_{DD}$ 

The positive supply current.

 $\mathbf{I}_{ss}$ 

The negative supply current.

 $V_D(V_S)$ 

The analog voltage on Terminal D and Terminal S.

RON

The ohmic resistance between Terminal D and Terminal S.

R<sub>FLAT(ON)</sub>

Flatness that is defined as the difference between the maximum and minimum value of on resistance measured over the specified analog signal range.

Is (Off)

The source leakage current with the switch off.

I<sub>D</sub> (Off)

The drain leakage current with the switch off.

 $I_D, I_S(On)$ 

The channel leakage current with the switch on.

 $\mathbf{V}_{\text{INI}}$ 

The maximum input voltage for Logic 0.

 $V_{\text{INH}}$ 

The minimum input voltage for Logic 1.

I<sub>INL</sub> (I<sub>INH</sub>)

The input current of the digital input.

Cs (Off)

The off switch source capacitance, which is measured with reference to ground.

CD (Off)

The off switch drain capacitance, which is measured with reference to ground.

 $C_D$ ,  $C_S$  (On)

The on switch capacitance, which is measured with reference to ground.

 $C_{IN}$ 

The digital input capacitance.

**t**transition

The delay time between the 50% and 90% points of the digital input and switch on condition when switching from one address state to another.

ton (EN)

The delay between applying the digital control input and the output switching on. See Figure 30.

toff (EN)

The delay between applying the digital control input and the output switching off. See Figure 30.

**Charge Injection** 

A measure of the glitch impulse transferred from the digital input to the analog output during switching.

Off Isolation

A measure of unwanted signal coupling through an off switch.

Crosstalk

A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.

Bandwidth

The frequency at which the output is attenuated by 3 dB.

On Response

The frequency response of the on switch.

**Insertion Loss** 

The loss due to the on resistance of the switch.

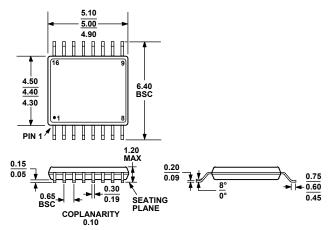
Total Harmonic Distortion + Noise (THD + N)

The ratio of the harmonic amplitude plus noise of the signal to the fundamental.

AC Power Supply Rejection Ratio (ACPSRR)

The ratio of the amplitude of signal on the output to the amplitude of the modulation. This is a measure of the ability of the part to avoid coupling noise and spurious signals that appear on the supply voltage pin to the output of the switch. The dc voltage on the device is modulated by a sine wave of  $0.62~\rm V~p\text{-}p$ .

## **OUTLINE DIMENSIONS**



#### COMPLIANT TO JEDEC STANDARDS MO-153-AB

Figure 33. 16-Lead Thin Shrink Small Outline Package [TSSOP] (RU-16) Dimensions shown in millimeters

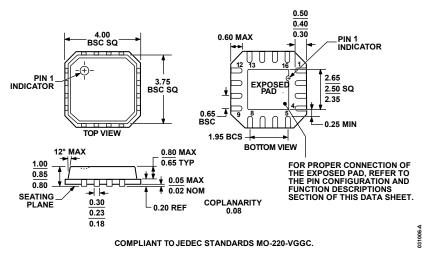


Figure 34. 16-Lead Lead Frame Chip Scale Package [LFCSP\_VQ] 4 mm × 4 mm Body, Very Thin Quad (CP-16-13) Dimensions shown in millimeters

#### **ORDERING GUIDE**

Model	Temperature Range	Package Description	Package Option
ADG1636BRUZ <sup>1</sup>	−40°C to +125°C	16- Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG1636BRUZ-REEL <sup>1</sup>	-40°C to +125°C	16- Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG1636BRUZ-REEL7 <sup>1</sup>	-40°C to +125°C	16- Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG1636BCPZ- REEL <sup>1</sup>	-40°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP_VQ]	CP-16-13
ADG1636BCPZ-REEL7 <sup>1</sup>	-40°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP_VQ]	CP-16-13

<sup>&</sup>lt;sup>1</sup> Z = RoHS Compliant Part.

